

Substitute for form 1449/PTO				<b>Complete if Known</b>	
				Application Number	10/514,429
				Filing Date	July 12, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	2881
				Examiner Name	M. J. Logie
Sheet	1	of	3	Attorney Docket Number	204552033800

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials*	Cts No.*	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
1.	US-5,306,662-A	04-26-1994	Nakamura et al.		
2.	US-6,177,292-B1	01-23-2001	Hong et al.		
3.	US-6,248,607-B1	06-19-2001	Tsutsui		
4.	US-6,355,497-B1	03-12-2002	Romano et al.		
5.	US-6,475,277-B1	11-05-2002	Hirata et al.		
6.	US-2002/0192507-A1	12-19-2002	Dwilinski et al.		
7.	US-6,627,552-B1	09-30-2003	Nishio et al.		
8.	US-6,639,925-B2	10-28-2003	Niwa et al.		
9.	US-6,653,663-B2	11-25-2003	Ishida		
10.	US-6,886,608-B1	02-03-2004	Takahira		
11.	US-6,693,935-B2	02-17-2004	Tojo et al.		
12.	US-2004/0089221-A1	05-13-2004	Dwilinski et al.		
13.	US-6,749,819-B2	06-15-2004	Otsuka et al.		
14.	US-2004/0238810-A1	12-02-2004	Dwilinski et al.		
15.	US-2004/0251471-A1	12-16-2004	Dwilinski et al.		
16.	US-2004/0261692-A1	12-30-2004	Dwilinski et al.		
17.	US-2005/0087124-A1	04-28-2005	Dwilinski et al.		
18.	US-2005/0249255-A1	11-10-2005	Dwilinski et al.		
19.	US-2006/0054075-A1	03-18-2006	Dwilinski et al.		
20.	US-2006/0054076-A1	03-16-2006	Dwilinski et al.		
21.	US-2006/0057749-A1	03-16-2006	Dwilinski et al.		
22.	US-2006/0124051-A1	06-15-2006	Yoshikote et al.		
23.	US-2006/0138431-A1	06-29-2006	Dwilinski et al.		
24.	US-7,132,730-B2	11-07-2006	Dwilinski et al.		
25.	US-7,252,712-B1	08-07-2007	Dwilinski et al.		
26.	US-7,314,517-B2	01-01-2008	Dwilinski et al.		
27.	US-7,335,262-B2	02-26-2008	Dwilinski et al.		
28.	US-2008/0050855-A1	02-28-2008	Dwilinski et al.		
29.	US-7,364,619-B2	04-29-2008	Dwilinski et al.		
30.	US-2008/0108162-A1	05-08-2008	Dwilinski et al.		
31.	US-7,374,615-B2	05-20-2008	Dwilinski et al.		
32.	US-7,387,677-B2	06-17-2008	Dwilinski et al.		
33.	US-2008/0156254-A1	07-03-2008	Dwilinski et al.		
34.	US-7,420,261-B2	09-02-2008	Dwilinski et al.		
35.	US-7,422,633-B2	09-09-2008	Dwilinski et al.		

<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials*	Cts No.*	Foreign Patent Document Country Code <sup>2</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
36.	JP-5-183189		07-23-1993	Nichia Kagaku Kogyo KK	Translation of abstract
37.	WO-94/28204		12-08-1994	Technalum Research, Inc.	
38.	WO-97/13891		04-17-1997	Centrum Badan Wysokociśnieniowych	

Substitute for form 1449/PTO				<i>Complete if Known</i>	
				Application Number	10/514,429
				Filing Date	July 12, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	2881
				Examiner Name	M. J. Logie
Sheet	2	of	3	Attorney Docket Number	204552033800

39.	JP-9-508093	08-19-1997		Corresponds to WO-94/28204 listed above
40.	JP-2001-077038	03-23-2001	Sumitomo Electric Industries	Translation of abstract and corresponds to US-6,475,277 listed above
41.	EP-1 164 210-A2	12-19-2001	Sharp Kabushiki Kaisha	
42.	JP-2002-026442	01-25-2002	Sony Corp.	Translation of abstract
43.	PL-347918	12-16-2002	AMMONO Sp. z o.o.; NICHIA CORPORATION	
44.	WO-02/101124-A1	12-19-2002	Nichia Corporation	Translation of abstract
45.	WO-03/035945	05-01-2003	Am-Mono SP. Z.O.; Nichia Corp.	
46.	PL-350375	05-05-2003	AMMONO Sp. z o.o.; NICHIA CORPORATION	
47.	EP-1 405 936-A1	04-07-2004	Ammono SP. Z.o.o	
48.	WO-2004/090202-A1	10-21-2004	Mitsubishi Chemical Corporation; Tokyo Denpa Co., Ltd.	Translation of abstract
49.	EP-1 616 981-A1	01-18-2006	Tokyo Denpa Co., Ltd.; Mitsubishi Chemical Corporation	

\*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages	
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages	<input checked="" type="checkbox"/>
	52.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages	<input checked="" type="checkbox"/>
	53.	Japanese Notification of Reason(s) for Refusal, mailed January 6, 2009, directed to Japanese Patent Application No. 2004-506101; 7 pages	<input checked="" type="checkbox"/>
	54.	International Search Report, mailed May 7, 2004, directed to International Patent Application No. PCT/JP03/15906; 3 pages	
	55.	International Search Report, mailed September 29, 2005, directed to International Patent Application No. PCT/JP2005/011091; 3 pages	
	56.	International Search Report, mailed April 21, 2006, directed to International Patent Application No. PCT/JP2005/022396; 3 pages	

Substitute for form 1449/PTO				<i>Complete if Known</i>	
				Application Number	10/514,429
				Filing Date	July 12, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	2881
				Examiner Name	M. J. Logie
Sheet	3	of	3	Attorney Docket Number 204552033800	

57.	U.S. Office Action, mailed October 16, 2007, directed to U.S. Patent Application No. 10/538,654; 10 pages
58.	U.S. Office Action, mailed April 2, 2007, directed to U.S. Patent Application No. 10/538,407;13 pages
59.	Song, Y. et al. (2003). "Bulk GaN Single Crystals: Growth Conditions by Flux Method." <i>Journal of Crystal Growth</i> . 247:275-279
60.	Beaumont, B. et al. (2001). "Epitaxial Lateral Overgrowth of GaN." <i>Phys. Stat. Sol.(b)</i> . 227(1):1-43
61. g	Liu, L. et al. (2002). "Substrates for Gallium Nitride Epitaxy." <i>Reports: A Review Journal, Materials Science and Engineering</i> :37:61-127
62.	Yano, M. et al. (2000). "Growth of Nitride Crystals, BN, AlN and GaN by Using a Na Flux" <i>Diamond and Related Materials</i> . 9:512-515
63.	Kelly, M. K. et al. (September 16, 1996). "Optical Patterning of GaN Films." <i>American Institute of Physics Appl. Phys. Lett.</i> 69:1749-1751
64.	Wong, S. W. et al. (September 6, 1999). "Fabrication of Thin-Film InGaN Light-Emitting Diode Membranes by Laser Lift-Off." <i>American Institute of Physics Applied Physics Letter</i> . 75(10):1360-1362
65.	Porowski, S. et al. (1993). "Prospects for High-Pressure Crystals Growth of III-V Nitrides." <i>Inst. Phys. Conf. Ser.</i> 134(4):369-372
66.	Peters, D. (1990). "Ammonothermal Synthesis of Aluminium Nitride." <i>Journal of Crystal Growth</i> . 104:411-418
67.	Inoue, T. et al. (2001). "Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method." <i>Journal of Crystal Growth</i> . 229:35-40
68.	Kolls, J. W. et al. (1998). "Materials Chemistry and Bulk Crystal Growth of Group III Nitrides in Supercritical Ammonia." <i>Materials Research Society Symp. Proc.</i> 495:367-372

Examiner Signature	Date Considered	
--------------------	-----------------	--

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>a</sup>Applicant's unique citation designation number (optional). <sup>b</sup>Applicant is to place a check mark here if English language Translation is attached.